

Program Overview

Room /Time	Bar/Living Room	Silver Creek
MoM		MBE-1MoM: Oxides and Nitrides MBE-2MoM: Heterogeneous Integration
MoA		MBE-1MoA: Novel Materials MBE-2MoA: Bismuthides and Antimonides
MoP	Poster Sessions	
TuM		MBE-1TuM: Technology of MBE MBE-2TuM: MBE Devices
TuA		MBE-1TuA: Layered Materials MBE-2TuA: Quantum Dots
WeM		MBE-1WeM: Superconductor/Semiconductor Interfaces MBE-2WeM: Heterostructures and Quantum Dots

Monday Morning, September 23, 2019

Room Silver Creek		
8:00am	INVITED: MBE-1MoM1 Oxide MBE Rocks!, <i>Darrell Schlom</i> , Cornell University	MBE Session MBE-1MoM Oxides and Nitrides Moderator: Jason Kawasaki, Univ. of Wisconsin Madison
8:15am	Invited talk continues.	
8:30am	Invited talk continues.	
8:45am	MBE-1MoM4 RF-plasma MBE Growth and Characterization of β -Ga ₂ O ₃ /NbN _x Heterostructures on SiC, <i>Neeraj Nepal</i> , D.S. Katzer, B. Downey, V.D. Wheeler, U.S. Naval Research Laboratory; <i>L. Nyakiti</i> , Texas A&M; <i>E. Jin</i> , V. Gokhale, M. Hardy, D. Storm, D. Meyer, U.S. Naval Research Laboratory	
9:00am	MBE-1MoM5 Development of a High-Purity, High-Concentration Ozone Delivery System for MBE and Growth of β -Ga ₂ O ₃ , <i>Mark O'Steen</i> , T. Campbell, S. Farrell, E. Tucker, D. Hanser, Veeco Instruments Inc.	
9:15am	MBE-1MoM6 Advancements in High Indium Content AlInN Grown Via Metal Modulated Epitaxy and Application Towards Polar/Non-Polar Optical Devices, <i>Zachary Engel</i> , E. Clinton, W.A. Doolittle, Georgia Institute of Technology	
9:30am	MBE-1MoM7 Structural and Electronic Properties of NbN and III-N/NbN Heterostructure Grown by Molecular Beam Epitaxy, <i>John Wright</i> , G. Khalsa, H.G. Xing, D. Jena, Cornell University	
9:45am	MBE-1MoM8 Optically-induced 2DEGs in GaN/AlGaN Heterostructures, <i>Stefan Schmult</i> , TU Dresden, Germany; <i>S. Wirth</i> , Max-Planck-Institute for Chemical Physics of Solids, Germany; <i>V. Solovyev</i> , Institute of Solid State Physics RAS, Russia; <i>R. Hentschel</i> , A. Wachowiak, NaMLab gGmbH; <i>T. Scheinert</i> , TU Dresden; <i>A. Grosser</i> , NaMLab gGmbH, Germany; <i>I. Kukushkin</i> , Institute of Solid State Physics RAS, Russia; <i>T. Mikolajick</i> , TU Dresden & NaMLab gGmbH, Germany	
10:00am	Break & Exhibits	
10:15am	Break & Exhibits	
10:30am	MBE-2MoM11 MBE Growth of High-Quality GaAs on C-plane Sapphire Substrate, <i>Samir Kumar Saha</i> , R. Kumar, A. Kuchuk, Y. Maidaniuk, Y. Mazur, S.Q. Yu, G. Salamo, University of Arkansas	MBE Session MBE-2MoM Heterogeneous Integration Moderator: Zbigniew Roman Wasilewski, Univ. of Waterloo
10:45am	MBE-2MoM12 Controlling Nucleation and Growth of IV-VI Rocksalt PbSe and PbSnSe on III-V Zincblende Substrates, <i>Brian Haidet</i> , E. Hughes, K. Mukherjee, University of California, Santa Barbara	
11:00am	MBE-2MoM13 LATE NEWS: Molecular Beam Epitaxy of AlN and GaN Nanocrystals: Towards High Efficiency Deep Ultraviolet LEDs, <i>Yuanpeng Wu</i> , A. Pandey, D.A. Laleyan, X. Liu, P. Wang, C. Ahn, M. Kira, Z. Mi, University of Michigan	
11:15am	MBE-2MoM14 Effectiveness of In _{0.1} Ga _{0.9} As Dislocation Filters to Reduce Threading Dislocation Density, <i>Chen Shang</i> , J. Norman, A. Gossard, J. Bowers, University of California, Santa Barbara	
11:30am	MBE-2MoM15 Study of Pit Formation in MBE Grown GaP on Misoriented Si Wafers, <i>Srinath Murali</i> , C. Zhang, R. King, C. Honsberg, Arizona State University	
11:45am	MBE-2MoM16 GaSb-Based Mid-Infrared Photonic Devices Monolithically Integrated onto Silicon, <i>Peter Carrington</i> , Lancaster University, UK	

Monday Afternoon, September 23, 2019

Room Silver Creek		
1:30pm	MBE-1MoA1 MBE Innovator Awardee Lecture, <i>Zbigniew Roman Wasilewski</i> , University of Waterloo, Canada	MBE Session MBE-1MoA Novel Materials Moderator: Kunal Mukherjee, Univ. of California, Santa Barbara
1:45pm	Talk continues.	
2:00pm	MBE-1MoA3 The Growth and Optical Properties of High Concentration of ErAs Embedded within GaAs, <i>Yuejing Wang, D. Wei, C. Ni, S. Law, J. Zide</i> , University of Delaware	
2:15pm	MBE-1MoA4 Varying MBE Growth Conditions to Limit Droplet Formation and Improve the Material Properties of TlGaAs Films, <i>Kevin Grossklaus, J. McElearney, M. Stevens, T. Vandervelde</i> , Tufts University	
2:30pm	MBE-1MoA5 Adsorption-controlled Epitaxial Growth of the Hyperferroelectric Candidate LiZnSb on GaSb (111), <i>Dongxue Du, P. Strohbeen, C. Zhang</i> , University of Wisconsin Madison; <i>H. Paik</i> , Cornell University; <i>P. Voyles, J. Kawasaki</i> , University of Wisconsin Madison	
2:45pm	MBE-1MoA6 Tuning the Electronic Structure of LuSb via Epitaxial Synthesis, <i>Shouvik Chatterjee</i> , University of California, Santa Barbara; <i>S. Khalid</i> , University of Delaware; <i>H. Inbar, A. Goswami</i> , University of California, Santa Barbara; <i>F. Crasto deLima, A. Sharan, F. Sabino</i> , University of Delaware; <i>T. Brown-Heft, Y-H. Chang</i> , University of California, Santa Barbara; <i>A. Fedorov</i> , Lawrence Berkeley National Laboratory; <i>D. Read</i> , Cardiff University, UK; <i>A. Janotti</i> , University of Delaware; <i>C. Palmstrøm</i> , University of California, Santa Barbara	
3:00pm	MBE-1MoA7 Programmable Magnetic Anisotropy in Ferromagnetic Semiconductor Films with Graded Composition, <i>Jacek Furdyna, S.-K. Bac, S. Dong, X. Liu, S. Rouvimov</i> , University of Notre Dame; <i>Y. Wang</i> , Nanjing University, China; <i>S. Lee</i> , Korea University, Republic of Korea; <i>M. Dobrowolska</i> , University of Notre Dame	
3:15pm	Break & Exhibit	
3:30pm	MBE-2MoA9 LATE NEWS: Minority Carrier Lifetime and Photoluminescence Properties of Mid-Wave InAsSbBi, <i>Preston T. Webster</i> , Air Force Research Laboratory; <i>P. Petluru</i> , University of Texas at Austin; <i>P.C. Grant</i> , Applied Technology Associates; <i>E.H. Steenbergen</i> , Air Force Research Laboratory; <i>D. Wasserman</i> , University of Texas at Austin	MBE Session MBE-2MoA Bismuthides and Antimonides Moderator: Joshua Zide, Univ. of Delaware
3:45pm	MBE-2MoA10 Characterization of Thick GaSbBi Layers Grown with Strain-stabilization, <i>Margaret Stevens, K. Grossklaus, J. McElearney, S. Lenney, T. Vandervelde</i> , Tufts University	
4:00pm	MBE-2MoA11 Comparing Droplet Formation and Phase Separation in Post-Saturation GaSbBi and GaAsBi, <i>John McElearney, K. Grossklaus, M. Stevens, T. Vandervelde</i> , Tufts University	
4:15pm	MBE-2MoA12 Molecular Beam Epitaxy Growth and Bandgap Measurements of InAsSbBi, <i>Stephen Schaefer, R.R. Kosireddy, S. Johnson</i> , Arizona State University	
4:30pm	MBE-2MoA13 Microstructure, Chemical Composition, and Surface Morphology of InAsSbBi Grown on GaSb by Molecular Beam Epitaxy, <i>Rajeev Reddy Kosireddy, S. Schaefer, S. Johnson</i> , Arizona State University	
4:45pm	MBE-2MoA14 Dislocation Dynamics as a Function of MBE Growth Conditions in Metamorphic InAsSb, <i>Stephanie Tomasulo</i> , Naval Research Laboratory; <i>C. Affouda, M. Twigg</i> , U.S. Naval Research Laboratory; <i>M. Yakes</i> , Naval Research Laboratory; <i>E. Aifer</i> , U.S. Naval Research Laboratory	

MBE

Room Bar/Living Room - Session MBE-MoP

MBE-Poster Session

5:00 pm

~~MBE-MoP1 Simultaneous Topographical And Electrochemical Mapping Using Scanning Ion Conductance Microscopy — Scanning Electrochemical Microscopy, G. Mendoza, Park Systems, Mexico; Byong Kim, K. Lee, Park Systems~~

MBE-MoP2 Doping and Surfactant Behavior of Gallium in Low-Temperature Silicon and Germanium Growth, **Amanda Lemire**, J. Manninen, J. Chivers, K. Grossklaus, T. Vandervelde, Tufts University

MBE-MoP3 Buffer layer growth for Si-Si on Si substrates using Molecular Beam Epitaxy, **Geun-Hwan Ryu**, Inha University, South Korea; J.D. Song, S.Y. Ahn, N.G. Hong, Korea Institute of Science and Technology, South Korea; H.Y. Ryu, Inha University, South Korea; W.J. Choi, Korea Institute of Science and Technology, South Korea

MBE-MoP4 Influence of Strain on InAsSb Composition, **Wendy Sarney**, S. Svensson, A. Leff, CCDC Army Research Laboratory; D. Donetsky, Stony Brook University

MBE-MoP5 Grading for Control of the Lattice Constant and Bandgap, as well as the Charge Distribution and Band Offsets at Interfaces, **Wendy Sarney**, S. Svensson, A. Leff, CCDC Army Research Laboratory; D. Donetsky, G. Kipshidze, L. Shterengas, G. Belenky, Stony Brook University

MBE-MoP6 Estimation of the Lateral Dimensions of Epitaxial CdSe/ZnSe Fractional Monolayer Quantum Dots, **Carlos Basilio**, Cinvestav-IPN, México; I. Hernández-Calderón, CINVESTAV, México

MBE-MoP7 Study of Conduction Mechanism using Temperature-Dependent Current-Voltage Measurements for GaAsSb Nanowire and Effect of In-situ Annealing, **Mehul Parakh**, S. Johnson, R. Pokharel, S. Devakoa, P. Ramaswamy, J. Li, S. Iyer, North Carolina A & T State University

MBE-MoP8 N-type Doping of GaAs Nanowires using GaTe Source Grown by Self Assisted Molecular Beam Epitaxy, **Shisir Devkota**, M. Parakh, P. Ramaswamy, North Carolina A & T State University; L. Reynolds, North Carolina State University; S. Iyer, North Carolina A & T State University

MBE-MoP9 Effect of Gold Coatings on Quantum Dot Emission, **Ariel Weltner**, C. Schuck, K. Vallejo, K. Sautter, T. Garrett, D. Tenne, P. Simmonds, Boise State University

MBE-MoP10 Nanostructure Mapping of GaAs and Ge (111)A Quantum Dots using Island Scaling and Radial Distribution Scaling Analysis, **Trent Garrett**, H. Henry, K. Sautter, K. Vallejo, C. Schuck, A. Weltner, E. Jankowski, P. Simmonds, Boise State University

MBE-MoP11 Optical Properties of InAs/GaAsSb Sub - Monolayer Quantum Dots with Various Sb Compositions, **Minseak Kim**, H.J. Jo, J.S. Kim, Yeungnam University, Republic of Korea; Y. Kim, S.J. Lee, Korea Research Institute of Standards and Science, Republic of Korea; C. Honsberg, Arizona State University

MBE-MoP12 LATE NEWS: Epitaxial Growth of Relaxed InGaN Films on ZnO Substrate by Plasma-Assisted Molecular Beam Epitaxy, **Kamruzzaman Khan**, E. Ahmadi, University of Michigan

MBE-MoP13 On the Origin of Hillock Formation during the Growth of InGaAs/InAlAs Superlattice on InP(111) Substrates, **Ida Sadeghi**, University of Waterloo, Canada; A. Pofelski, G.B. Botton, McMaster University, Canada; Z.R. Wasilewski, University of Waterloo, Canada

MBE-MoP14 LATE NEWS: Graphene/III-V Hybrid Diodes and Optical Devices by Heteroepitaxy, **R. Yao**, B. Zheng, University of Massachusetts Lowell; H. Kum, Y. Kim, S. Bae, J. Kim, Massachusetts Institute of Technology; H. Zhang, University of Massachusetts Lowell; S. Xia, Georgia Institute of Technology; **Wei Guo**, University of Massachusetts Lowell

MBE-MoP15 LATE NEWS: The Role of Intervalley Phonons in Hot-Carrier Transfer and Extraction in InAs/AlAs_{0.16}Sb_{0.84} Quantum-Well Solar Cells, V.R. Whiteside, H. Esmailpour, **Kyle R. Dorman**, T.D. Mishima, University of Oklahoma; D.K. Ferry, Arizona State University; M.B. Santos, I.R. Sellers, University of Oklahoma

Tuesday Morning, September 24, 2019

Room Silver Creek	
8:15am	INVITED: MBE-1TuM1 Antimonide Heterostructures for Thermophotovoltaics, Hot-Carrier Solar Cells, and Quantum Hall Ferromagnetism, <i>Tetsuya D. Mishima, Jeremy A. Massengale, and Michael B. Santos</i> , Homer L. Dodge Department of Physics and Astronomy, University of Oklahoma
8:30am	Talk continues.
8:45am	MBE-1TuM3 Growth-Induced Temperature Changes During Transition Metal Nitride Epitaxy on Transparent SiC Substrates, <i>D. Scott Katzer, M. Hardy, N. Nepal, D. Storm, B. Downey, E. Jin, D. Meyer</i> , U.S. Naval Research Laboratory
9:00am	MBE-1TuM4 Using the Desorption Mass Spectrometry Technique to Optimize Sb Flux in GaSbBi Growth, <i>Jedidiah McCoy, C. Lu, R. Kaspi</i> , Air Force Research Laboratory
9:15am	MBE-1TuM5 BBr_2 as a B Source in Plasma-Assisted MBE, <i>Richard Cramer, B. Bonef, J. Speck</i> , University of California, Santa Barbara
9:30am	MBE-1TuM6 Assessing MBE Regrowth Quality on Transfer Printed Virtual Substrates, <i>Michael Yakes</i> , Naval Research Laboratory; <i>M. Lumb, M. Bennett</i> , George Washington University; <i>J. Nolde, S. Tomasulo</i> , Naval Research Laboratory; <i>C. Haughn</i> , Army Research Laboratory; <i>S. Mack, S. Maximenko, K. Schmieder</i> , Naval Research Laboratory
9:45am	MBE-1TuM7 LATE NEWS: Mechanism of Si Doping in O_2 Plasma-Assisted MBE Growth of $\beta\text{-Ga}_2\text{O}_3$, <i>Nidhin Kurian Kalarickal, Z. Xia, J. McGlone, S. Krishnamoorthy, W. Moore, M. Brenner, A.R. Arehart, S.A. Ringel, S. Rajan</i> , The Ohio State University
10:00am	Break & Exhibits
10:15am	Break & Exhibits
10:30am	MBE-2TuM10 Development of AlAsSb Digital Alloys on GaSb and InP Substrates for Photo-Detector Applications, <i>Baolai Liang, B.C. Juang, M. Debnath, D. Huffaker</i> , University of California, Los Angeles
10:45am	MBE-2TuM11 Structural and Optical Properties of Bulk nBn InAsSb Metamorphic Detector, <i>Vinita Dahiya, Z. Taghipour, A. Blumer</i> , The Ohio State University; <i>D. Lubyshev, J. Fastenau, A. Liu</i> , IQE Inc.; <i>T. Grassman, S. Krishna</i> , The Ohio State University
11:00am	MBE-2TuM12 All-Epitaxial Mid-Wavelength Infrared Resonant Cavity-Enhanced Photodiodes, <i>Gregory Savich, G. Wicks, J. Shao, K. Jamison, L. Fredin, T. Golding</i> , Amethyst Research Inc.; <i>M. Carmichael</i> , Amethyst Research Ltd., UK; <i>A. Craig, F. Al-Saymari, A. Marshall</i> , Lancaster University, UK
11:15am	MBE-2TuM13 Molecular Beam Epitaxy of Coalesced AlGaIn Nanowires: Ultraviolet Transparent Electrodes for Large-Area LEDs, <i>Brelon May</i> , National Renewable Energy Laboratory; <i>E. Hettiaratchy, B. Wang, C. Selcu, B. Esser, D. McComb, R. Myers</i> , The Ohio State University
11:30am	MBE-2TuM14 High Peak-current Density AlN/GaN Resonant Tunnel Diodes Grown by rf-MBE on GaN Templates, <i>David Storm</i> , U.S. Naval Research Laboratory; <i>T. Growden</i> , Naval Research Laboratory; <i>E. Cornuelle, L. Whitaker</i> , The Ohio State University; <i>P. Peri</i> , Arizona State University; <i>W. Zhang</i> , Wright State University; <i>J. Daulton</i> , Massachusetts Institute of Technology; <i>D.S. Katzer, M. Hardy, N. Nepal</i> , U.S. Naval Research Laboratory; <i>R. Molnar</i> , Massachusetts Institute of Technology; <i>E. Brown</i> , Wright State University; <i>P. Berger</i> , The Ohio State University; <i>D. Meyer</i> , U.S. Naval Research Laboratory; <i>D. Smith</i> , Arizona State University
11:45am	MBE-2TuM15 Optimized Material for Intermediate Band Solar Cells: Type-II CdTe Quantum Dots in a ZnCdSe Matrix, <i>Vasilios Deligiannakis</i> , The City College of New York/Graduate Center of CUNY; <i>M. Begliarbekov</i> , CUNY Advanced Science Research Center; <i>S. Alsheimer</i> , City College of New York, City University of New York; <i>I. Kuskovsky</i> , Queens College; <i>M. Tamargo</i> , City College of New York, City University of New York

MBE Session MBE-1TuM

Technology of MBE

Moderator: Sanjay Krishna, The Ohio State Univ.

MBE Session MBE-2TuM

MBE Devices

Moderator: Songrui Zhao, McGill Univ.

Tuesday Afternoon, September 24, 2019

Room Silver Creek		
1:30pm	MBE-1TuA1 MBE Young Investigator Awardee Lecture, <i>Jason Kawasaki</i> , University of Wisconsin Madison	MBE Session MBE-1TuA Layered Materials Moderator: Stephanie Tomasulo, Naval Research Lab
1:45pm	Talk continues.	
2:00pm	MBE-1TuA3 Band Engineering to Achieve a Wide Band Gap Topological Insulator, <i>Ido Levy, C. Youmans, T. Garcia, H. Deng, S. Alsheimer, L. Krusin-Elbaum, P. Ghaemi, M. Tamargo</i> , City College of New York, City University of New York	
2:15pm	MBE-1TuA4 Van der Waal Epitaxy of Bi ₂ Se ₃ on GaAs: A Morphological Playground, <i>Theresa Ginley, S. Law</i> , University of Delaware	
2:30pm	MBE-1TuA5 Growth of GeTe and Sb ₂ Te ₃ Interlayer Structures for Interfacial Phase Change Devices via Molecular Beam Epitaxy, <i>Adrian Podpirka, D. Shrekenhamer, C. Zgrabik, J. Pierce, J. Gagnon</i> , JHU/APL	
2:45pm	MBE-1TuA6 Molecular Beam Epitaxy of Hexagonal Boron Nitride on HOPG, <i>Ping Wang, E.T. Reid, D.A. Laleyan, J. Gim, Q. Wen, Z. Liu, Z. Zhong, M. Kira, R. Hovden, Z. Mi</i> , University of Michigan	
3:00pm	Break & Exhibits	
3:15pm	Break & Exhibits	
3:30pm	MBE-2TuA9 InAs Chirped Quantum Dot Growth on Si for Broadband Spectral Gain Mode--locked Laser, <i>Daehwan Jung</i> , Korea Institute of Science and Technology, Republic of Korea; <i>J. Norman, C. Shang, S. Tao, Y. Wan, A. Gossard, J. Bowers</i> , University of California, Santa Barbara	MBE Session MBE-2TuA Quantum Dots Moderator: Paul Simmonds, Boise State Univ.
3:45pm	MBE-2TuA10 InP Quantum Dots for Dislocation-tolerant, Visible Light Emitters on Si, <i>Pankul Dhingra</i> , University of Illinois Urbana-Champaign; <i>Y. Sun</i> , Yale University; <i>S. Fan, R. Hool, M.L. Lee</i> , University of Illinois Urbana-Champaign	
4:00pm	MBE-2TuA11 Gallium-assisted Deoxidation for Spatially and Spectrally Controlled InAs Quantum Dot Molecules, <i>Lauren McCabe, J. Zide</i> , University of Delaware	
4:15pm	MBE-2TuA12 Influence of the Growth Conditions on the Performance of InAs Sub-Monolayer Quantum Dot Infrared Photodetectors, <i>Kevin Vallejo</i> , Boise State University; <i>A. Zeidan, T. Cantalice, A. Quivy</i> , University of Sao Paulo, Brazil; <i>P. Simmonds</i> , Boise State University	
4:30pm	MBE-2TuA13 Effect of Annealing on Structure and Luminescence of InP/AlGaInP Quantum Dots, <i>Pankul Dhingra</i> , University of Illinois Urbana-Champaign; <i>Y. Sun</i> , Yale University; <i>E. Moog, M.L. Lee</i> , University of Illinois Urbana-Champaign	
4:45pm	MBE-2TuA14 Structural and Optical Properties of GaAs(111)A Tensile-strained Quantum Dots using As ₂ and As ₄ , <i>Christopher Schuck</i> , University of Delaware; <i>K. Vallejo, T. Garrett</i> , Boise State University; <i>Q. Wang, Y. Wang, B. Liang</i> , Hebei University, China; <i>P. Simmonds</i> , Boise State University	
5:00pm	MBE-2TuA15 Comparing the Self-assembly of Tensile-strained Ge and GaAs Quantum Dots on InAlAs(111)A, <i>Kathryn Sautter, C. Schuck, T. Garrett, K. Vallejo, A. Weltner</i> , Boise State University; <i>J. Smith, C. Ratsch</i> , University of California, Los Angeles; <i>P. Simmonds</i> , Boise State University	

Wednesday Morning, September 25, 2019

Room Silver Creek		
8:15am	INVITED: MBE-1WeM1 Towards Topological Qubits with MBE-grown Heterostructures, <i>Michael Manfra</i> , Purdue University	MBE Session MBE-1WeM Superconductor/Semiconductor Interfaces Moderator: Christopher Schuck, Univ. of Delaware
8:30am	Invited talk continues.	
8:45am	MBE-1WeM3 Aluminum Metallization of III-V Semiconductors for the Study of Proximity Superconductivity, <i>Wendy Sarney, S. Svensson, A. Leff</i> , CCDC Army Research Laboratory; <i>J. Yuan, W. Mayer, K. Wickramasinghe, J. Shabani</i> , New York University	
9:00am	MBE-1WeM4 Epitaxy and Characterization of Superconducting Aluminum Films on InAs Quantum Well Heterostructures, <i>Tiantian Wang</i> , Purdue University	
9:15am	MBE-1WeM5 Transport Properties of Superconductor- Ferromagnetic-Semiconductor Heterostructures, <i>Kaushini Wickramasinghe, J. Yuan, K. Sardashti, M. Dartailh, W. Mayer</i> , New York University; <i>M. Jiang, L. Anh, M. Tanaka, S. Ohya</i> , University of Tokyo, Japan; <i>V. Manucharyan</i> , University of Maryland; <i>J. Shabani</i> , New York University	
9:30am	MBE-1WeM6 LATE NEWS: Van der Waals Epitaxy of High Quality AlN towards Deep Ultraviolet Light Emitting Diodes on Monolayer Graphene, <i>Ping Wang, A. Pandey, E.T. Reid, J. Gim, W.J. Shin, D.A. Laleyan, D. Zhang, Y. Sun, Z. Zhong, R. Hovden</i> , University of Michigan	
9:45am	MBE-1WeM7 LATE NEWS: Determination of Background Doping Type in Type-II Superlattice using Capacitance-Voltage Technique with Double Mesa Structure, <i>Seunghyun Lee, D.R. Fink, S.H. Kodati, V. Dahiya, T.J. Ronningen</i> , The Ohio State University; <i>M. Winslow, C.H. Grein</i> , University of Illinois at Chicago; <i>A.H. Jones, J.C. Campbell</i> , University of Virginia; <i>J.F. Klem</i> , Sandia National Laboratories; <i>S. Krishna</i> , The Ohio State University	
10:00am	Break	
10:15am	Break	
10:30am	MBE-2WeM10 Vertical Hole Transport in InAs/InAs _{1-x} Sb _x Type-II Superlattices, <i>Cheng-Ying Tsai, Y. Zhang, Z. Ju, Y.-H. Zhang</i> , Arizona State University	
10:45am	MBE-2WeM11 Room Temperature THz Intersubband Transitions in Continuously-graded Al _x Ga _{1-x} As Parabolic Quantum Well Arrays, <i>C. Deimert</i> , University of Waterloo, Canada; <i>P. Goulain, J.-M. Manceau, A. Bousseksou</i> , CNRS and University of Paris-Sud, France; <i>W. Pasek, T. Yoon, N.Y. Kim</i> , University of Waterloo, Canada; <i>R. Colombelli</i> , CNRS and University of Paris-Sud, France; <i>Zbigniew Roman Wasilewski</i> , University of Waterloo, Canada	MBE Session MBE-2WeM Heterostructures and Quantum Dots Moderator: Stephanie Law, Univ. of Delaware
11:00am	MBE-2WeM12 Excitonic Properties of Asymmetric Triple CdSe Quantum Wells, <i>F. Hernández-García</i> , Cinvestav-IPN, México; <i>F. Sutara, Isaac Hernández-Calderón</i> , CINVESTAV, México	
11:15am	MBE-2WeM13 Gain Measurements of Se-based II-VI Multiple Quantum Well Structures for Vertical-External-Cavity Surface-Emitting Laser Applications, <i>K. Zhao</i> , The City College of New York; <i>G. Chappell, J. Hastie</i> , University of Strathclyde, UK; <i>S.K. Gayen</i> , The City College of New York/Graduate Center of CUNY; <i>Maria Tamargo</i> , City College of New York, City University of New York	
11:30am	MBE-2WeM14 Structural and Optical Properties of PbTe/CdTe/InSb Heterostructures Grown using Molecular Beam Epitaxy, <i>Tyler McCarthy</i> , Arizona State University	